Inventor: Leonard Forbes

Title: Electronic Apparatus, Silicon-On-Insulator Integrated Circuits, and Fabrication Methods

Assignee: Micron Technology, Inc.

Docket No. MI22-2272

INFORMATION DISCLOSURE STATEMENT

References -- See Attached Form PTO-1449

REMARKS

The citations listed, copies attached except for U. S. Patents, may be material to the examination of the subject application and are therefore submitted in compliance with the duty of disclosure defined in 37 CFR §1.56. The Examiner is requested to make these citations of official record in this application. No admission is made regarding

The materials cited are presented to assist in and expedite examination of this application. The present invention is considered to be patentable over the cited materials. Expeditious examination and allowance of this application as a patent are therefore urged in order that the public may benefit from the disclosure and commercialization of the invention.

Respectfully submitted,

Dated: 24 Sep 2003

Attorney: _____
James E. Lake
Reg. No.: 44,854

EV085414133

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-2272	SERIAL NO. Filed Herewith
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT Leonard Forbes	
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U.S. PATENT DOCUMENTS

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	AM							
	AN							
	AO							
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	AQ							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

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Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. M122-2272	SERIAL NO. Filed Herewith
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		FILING DATE Filed Herewith	GROUP Unknown

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